

# Alison Baski

## List of Publications by Year in descending order

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51  
papers

3,138  
citations

136950

32  
h-index

189892

50  
g-index

51  
all docs

51  
docs citations

51  
times ranked

2504  
citing authors

#	ARTICLE	IF	CITATIONS
1	Growth of Self-Assembled n-Alkyltrichlorosilane Films on Si(100) Investigated by Atomic Force Microscopy. Langmuir, 1995, 11, 2143-2150.	3.5	200
2	The structure of silicon surfaces from (001) to (111). Surface Science, 1997, 392, 69-85.	1.9	177
3	Aluminum on the Si(100) surface: Growth of the first monolayer. Physical Review B, 1991, 44, 1415-1418.	3.2	173
4	The Origin of the Superstructure in Bi <sub>2</sub> Sr <sub>2</sub> CaCu <sub>2</sub> O <sub>8</sub> +dgr as Revealed by Scanning Tunneling Microscopy. Science, 1988, 242, 1673-1675.	12.6	164
5	Surface extended-x-ray-absorption fine structure and scanning tunneling microscopy of Si(001)2 $\times$ 1-Sb. Physical Review Letters, 1990, 65, 3417-3420.	7.8	141
6	Highly Efficient Electron Field Emission from Graphene Oxide Sheets Supported by Nickel Nanotip Arrays. Nano Letters, 2012, 12, 1265-1268.	9.1	140
7	$\sqrt{3} \times \sqrt{3}$ $\sqrt{6} \times \sqrt{6}$ phase transition on the Au/Si(111) surface. Physical Review Letters, 1990, 65, 1611-1614.	7.8	123
8	Dependence of GaN polarity on the parameters of the buffer layer grown by molecular beam epitaxy. Applied Physics Letters, 2001, 78, 4145-4147.	3.3	122
9	A Stable High-Index Surface of Silicon: Si(5 5 12). Science, 1995, 269, 1556-1560.	12.6	116
10	Indium-induced reconstructions of the Si(100) surface. Physical Review B, 1991, 43, 9316-9319.	3.2	105
11	Epitaxial growth of silver on mica as studied by AFM and STM. Surface Science, 1994, 313, 275-288.	1.9	102
12	Tin-induced reconstructions of the Si(100) surface. Physical Review B, 1991, 44, 11167-11177.	3.2	89
13	Quasiperiodic Nanoscale Faceting of High-Index Si Surfaces. Physical Review Letters, 1995, 74, 956-959.	7.8	86
14	Structure and Stability of Si(114) $\sqrt{2} \times \sqrt{2}$ . Physical Review Letters, 1996, 77, 687-690.	7.8	86
15	Surface photovoltage in undoped n-type GaN. Journal of Applied Physics, 2010, 107, .	2.5	86
16	Si(111)-5 $\times$ 1-Au reconstruction as studied by scanning tunneling microscopy. Physical Review B, 1990, 41, 10247-10249.	3.2	84
17	Epitaxial lateral overgrowth of (112 $\sqrt{2}$ ) semipolar GaN on (11 $\sqrt{00}$ ) m-plane sapphire by metalorganic chemical vapor deposition. Applied Physics Letters, 2007, 90, 182109.	3.3	82
18	1-D nanostructures grown on the Si(5 5 12) surface. Applied Surface Science, 2001, 182, 216-222.	6.1	72

#	ARTICLE	IF	CITATIONS
19	Morphology and electronic structure of the Ca/Si(111) system. Surface Science, 2001, 476, 22-34.	1.9	67
20	Bi on Si(111): Two phases of the $\sqrt{3} \times \sqrt{3}$ surface reconstruction. Physical Review B, 1993, 48, 4895-4898.	3.2	64
21	Photoadsorption and photodesorption for GaN. Applied Physics Letters, 2009, 94, 162116.	3.3	63
22	Surface band bending of a-plane GaN studied by scanning Kelvin probe microscopy. Applied Physics Letters, 2006, 88, 122104.	3.3	61
23	Investigation of forward and reverse current conduction in GaN films by conductive atomic force microscopy. Applied Physics Letters, 2004, 84, 4150-4152.	3.3	56
24	Defect reduction in (112 $\bar{0}$ ) a-plane GaN by two-stage epitaxial lateral overgrowth. Applied Physics Letters, 2006, 89, 262105.	3.3	55
25	Adsorption-site determination of ordered Yb on Si(111) surfaces. Physical Review B, 1993, 47, 9663-9668.	3.2	54
26	Comparative study of the (0001) and (0001 $\bar{A}$ ) surfaces of ZnO. Applied Physics Letters, 2006, 89, 182111.	3.3	54
27	Study of SiN <sub>x</sub> and SiO <sub>2</sub> passivation of GaN surfaces. Journal of Applied Physics, 2007, 101, 113709.	2.5	52
28	Frenkel-Kontorova Model of Vacancy-Line Interactions on Ga/Si(112). Physical Review Letters, 1999, 83, 1818-1821.	7.8	50
29	Investigation of inversion domains in GaN by electric-force microscopy. Applied Physics Letters, 2001, 78, 2497-2499.	3.3	46
30	The effect of hydrogen etching on 6H-SiC studied by temperature-dependent current-voltage and atomic force microscopy. Applied Physics Letters, 2004, 85, 1547-1549.	3.3	38
31	Current mapping of GaN films by conductive atomic force microscopy. Applied Physics Letters, 2003, 82, 1890-1892.	3.3	37
32	Nonpolar m-plane GaN on patterned Si(112) substrates by metalorganic chemical vapor deposition. Applied Physics Letters, 2009, 95, .	3.3	37
33	The structure of Si(112):Ga-( $\sqrt{3} \times \sqrt{3}$ ) reconstructions. Surface Science, 1999, 423, L265-L270.	1.9	34
34	STM studies of 1-D noble metal growth on silicon. Ultramicroscopy, 2001, 86, 23-30.	1.9	26
35	Au-induced faceting of the Si(5512) surface. Surface Science, 2004, 561, 193-199.	1.9	22
36	Internal quantum efficiency of c-plane InGaN and m-plane InGaN on Si and GaN. Applied Physics Letters, 2009, 95, 101106.	3.3	22

#	ARTICLE	IF	CITATIONS
37	Defect reduction with quantum dots in GaN grown on sapphire substrates by molecular beam epitaxy. Applied Physics Letters, 2002, 80, 216-218.	3.3	20
38	Electronic behavior of the Zn- and O-polar ZnO surfaces studied using conductive atomic force microscopy. Journal of Applied Physics, 2009, 105, .	2.5	18
39	Fabrication of Solâ~Gel Materials with Anisotropic Physical Properties by Photo-Cross-Linking. Chemistry of Materials, 2009, 21, 2108-2114.	6.7	18
40	Investigation of Defects and Polarity in GaN Using Hot Wet Etching, Atomic Force and Transmission Electron Microscopy and Convergent Beam Electron Diffraction. Physica Status Solidi (B): Basic Research, 2001, 228, 513-517.	1.5	16
41	Role of the surface in the electrical and optical properties of GaN. Physica B: Condensed Matter, 2009, 404, 4892-4895.	2.7	16
42	Observation of surface charging at the edge of a Schottky contact. IEEE Electron Device Letters, 2006, 27, 211-213.	3.9	14
43	Polarity of GaN Grown on Sapphire by Molecular Beam Epitaxy with Different Buffer Layers. Physica Status Solidi A, 2001, 188, 571-574.	1.7	12
44	Effects of hydrogen on the morphology and electrical properties of GaN grown by plasma-assisted molecular-beam epitaxy. Applied Physics Letters, 2005, 86, 121914.	3.3	11
45	A Comparative Study of MBE-Grown GaN Films Having Predominantly Ga- or N-Polarity. Physica Status Solidi (B): Basic Research, 2001, 228, 543-547.	1.5	8
46	Dielectric anomalies related to domain walls in ferroelectric CsD2AsO4. Ferroelectrics, Letters Section, 1987, 7, 171-178.	1.0	7
47	Electrochemically self-assembled nanostructure arrays. Journal of Crystal Growth, 2004, 268, 342-345.	1.5	7
48	Transient photovoltage in GaN. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 2813-2816.	0.8	3
49	Where is the V=0 equipotential?. American Journal of Physics, 1986, 54, 854-854.	0.7	1
50	Effect of Temperature on the Growth of InAs/GaAs Quantum Dots Grown on a Strained GaAs Layer. Journal of Nanoscience and Nanotechnology, 2007, 7, 2889-2893.	0.9	1
51	Oversight. Physics Teacher, 1985, 23, 396-396.	0.3	0